PCN Number: 2			201	20150804002			F	PCN Date:		08/11/2015	
Title: TAS5760L Die Revision Change											
Customer Contact:				PCN Manager De			De	ept: Q		Qual	ity Services
Proposed 1 st Ship Date			:	11/11/2015Estimated Sample Availability:			Date provided at sample request.				
Change Type:											
Assembly Site				Assembly Process			Assembly Materials				
Design			[Electrical Specification			Mechanical Specification				
Test Site				Packing/Shipping/Labeling			Test Process				
Wafer Bump Site				Wafer Bump Material			Wafer Bump Process				
Wafer Fab Site				Wafer Fab Materials			Wafer Fab Process				
	Part number change										
PCN Details											

Description of Change:

This notification is to announce a die revision and datasheet change to the devices listed in the Product Affected Section of this document. The new die provides clocking improvements that allow the MCLK pin to be tied directly to SCLK for some clock ratios. The die also includes changes of the class-D output FET's from a 30V Fab component to a 20V Fab component.

The Die Revision and the datasheet number will be changing:

TAS5760L:

Current		New			
Die Revision	Datasheet Number	Die Revision	Datasheet Number		
В	SLOS782A	C	SLOS782B		

The product datasheet(s) is updated as seen in the change revision history below:



TAS5760L

SLOS782B-JULY 2013-REVISED JULY 2015

TAS5760L General-Purpose I2S Input Class-D Amplifier

Changes from Revision A (October 2013) to Revision B

Page

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•	Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section
•	Changed Features list item, Audio Performance From: R _{LOAD} = 8Ω To: R _{SPK} = 8Ω1
•	Changed From: Voltage at speaker amplifier output pins To: Speaker Amplifier Output Voltage in the Abs Max table 6
•	Modified Master clock and Serial Audio Port specifications to reflect the clocking improvements of the device

These changes may be reviewed at the datasheet link provided: <u>http://www.ti.com/lit/ds/symlink/tas5760l.pdf</u>

TAS5760LD:							
Current		New					
Die Revision	Datasheet Number	Die Revision	Datasheet Number				
В	SLOS781	С	SLOS781A				
Texas Instruments			TAS5760LD SLOS781A-JULY 2013-REVISED JULY 2015 Th DirectPath™ Headphone				
Changes from Original (Jul	y 2013) to Revision A		Page				
Modes, Application and In and Documentation Supp	nplementation section, Power S ort section, and Mechanical, Pa	upply Recommendations ckaging, and Orderable I	iption section, Device Functional section, Layout section, Device nformation section				
	These changes may be reviewed at the datasheet links provided: http://www.ti.com/lit/ds/symlink/tas5760ld.pdf						
Reason for Change:							
Improved product perf	ormance						
Anticipated impact of	on Form, Fit, Function	, Ouality or Relia	ability (positive / negative):				
None							
	identification resultin	ng from this PCN	•				
	I change as shown in th						
Current Die Rev [2P] B	New Die Rev [2P] C						
Sample product shipping label to indicate die rev location (not actual product label) TEXAS INSTRUMENTS MADE IN: Malaysia 2DC: 2Q: MSL 2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04 OPT: ITEM: BL: 5A (L)T0:1750 (0) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY (1T) 7523483S12 (2P) REV: (2D) CS0: SHE (21L) CC0:USA (23L) AGO: MYS							
Product Affected:							
TAS5760LDAP	TAS5760LDCA	TAS5760LDDCA	TAS5760LDDCAR				
TAS5760LDAPR	TAS5760LDCAR						

Qualification Report

TAS5760LDAP, TAS5760LDCA, TAS5760LDDCA Die Change Approve Date 30-Jun-2015

Product Attributes

Attributes	Qual Device: TAS5760LDAP	Qual Device: TAS5760LDCA	Qual Device: TA\$5760LDDCA
Assembly Site	TAI	TAI	TAI
Package Family	HTQFP	HTSSOP	HTSSOP
Wafer Fab Supplier	RFAB	RFAB	RFAB
Wafer Process	LBC7	LBC7	LBC7

- QBS: Qual By Similarity

- Qual Devices gualified at LEVEL3-260C: TAS5760LDAP, TAS5760LDCA, TAS5760LDDCA

- Device TAS5760LDDCA contains multiple dies.

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: TAS5760LDAP	Qual Device: TAS5760LDCA	Qual Device: TAS5760LDDCA
ED	Electrical Characterization	Per Datasheet Parameters	Pass	Pass	-
HBM	ESD-HBM	4000 V	1/3/0	1/3/0	1/3/0
CDM	ESD-CDM	1500 V	1/3/0	1/3/0	1/3/0
LU	Latch-up	(per JESD78)	1/6/0	1/6/0	1/6/0
тс	Temperature Cycle, - 65/150C	500 Cycles	1/77/0	1/77/0	-
WBP	Bond Pull	Wires	1/76/0	1/76/0	-
WBS	Ball Bond Shear	Wires	1/76/0	1/76/0	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com